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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	75
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2138acnfp-v0

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

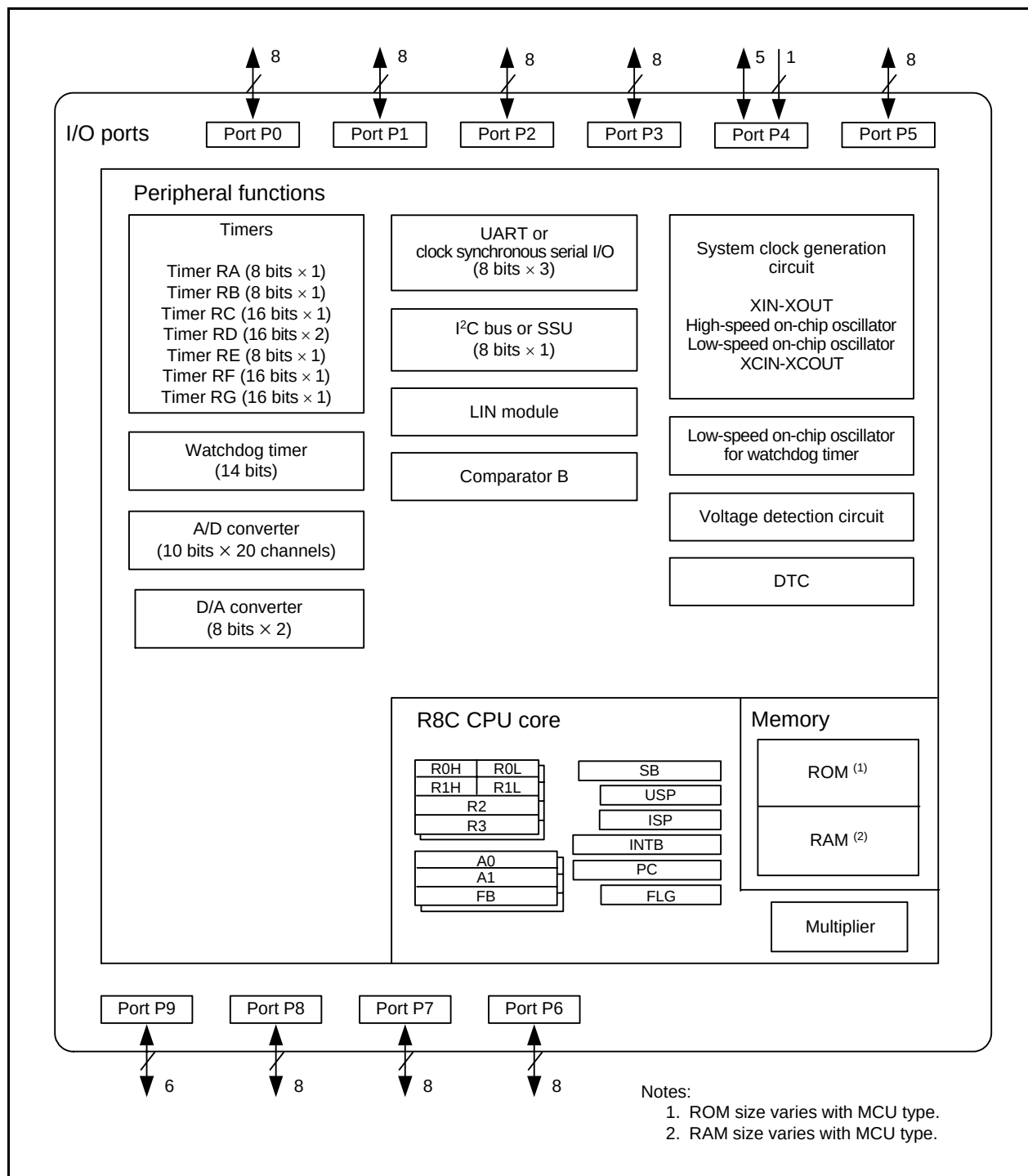


Figure 1.2 Block Diagram

Table 1.7 Pin Functions (2)

Item	Pin Name	I/O Type	Description
SSU	SSI	I/O	Data I/O pin.
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin.
	SSCK	I/O	Clock I/O pin.
	SSO	I/O	Data I/O pin.
I ² C bus	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter.
A/D converter	AN0 to AN19	I	Analog input pins to A/D converter.
	$\overline{\text{ADTRG}}$	I	AD external trigger input pin.
D/A converter	DA0, DA1	O	D/A converter output pins.
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins.
	IVREF1, IVREF3	I	Comparator B reference voltage input pins.
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program.
Input port	P4_2	I	Input-only port.

I: Input O: Output I/O: Input and output

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

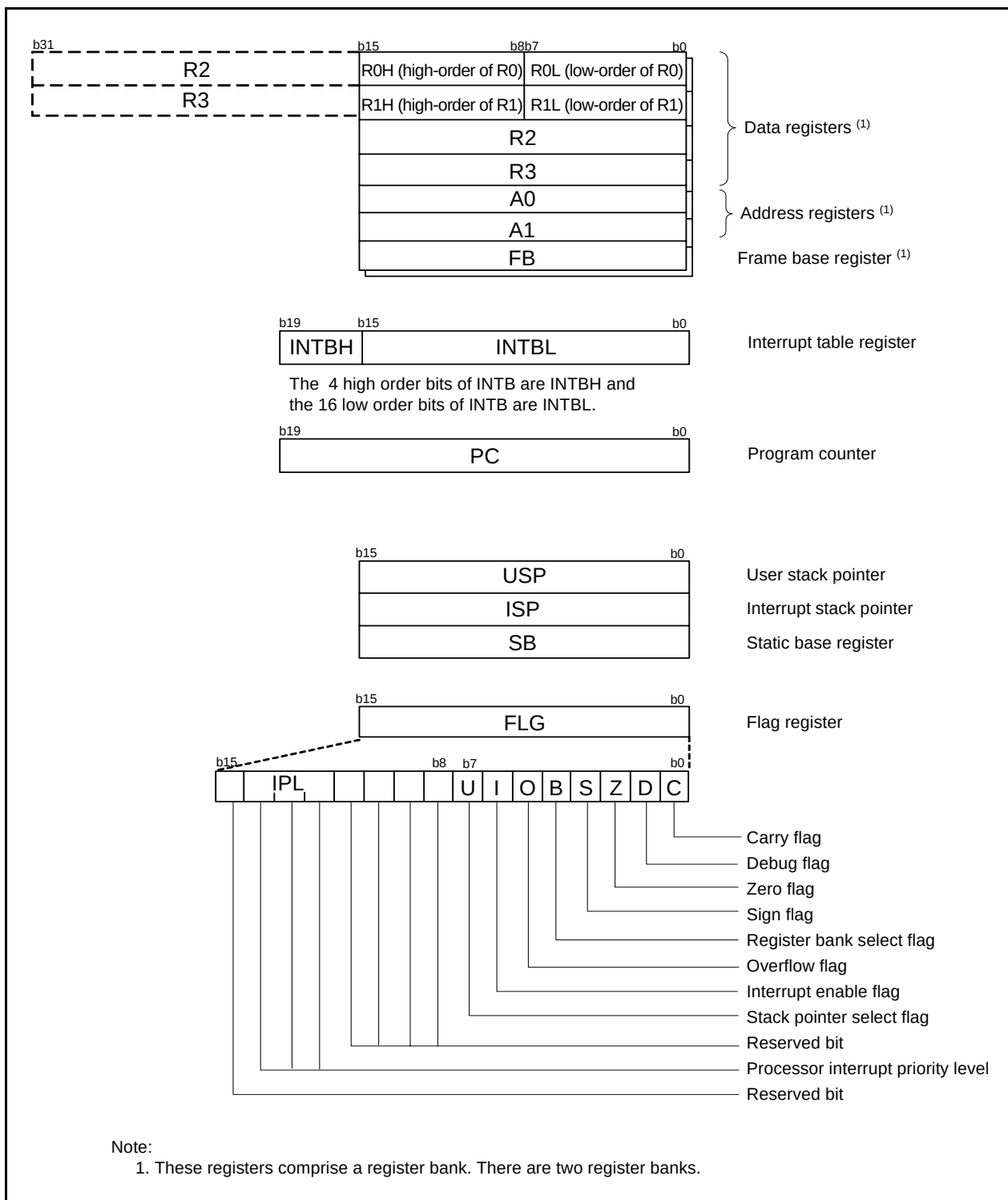


Figure 2.1 CPU Registers

Table 4.6 SFR Information (6) (1)

Address	Register	Symbol	After Reset
0140h	Timer RD Control Register 0	TRDCR0	00h
0141h	Timer RD I/O Control Register A0	TRDIORA0	10001000b
0142h	Timer RD I/O Control Register C0	TRDIORC0	10001000b
0143h	Timer RD Status Register 0	TRDSR0	11100000b
0144h	Timer RD Interrupt Enable Register 0	TRDIER0	11100000b
0145h	Timer RD PWM Mode Output Level Control Register 0	TRDPOCR0	11111000b
0146h	Timer RD Counter 0	TRD0	00h
0147h			00h
0148h	Timer RD General Register A0	TRDGRA0	FFh
0149h			FFh
014Ah	Timer RD General Register B0	TRDGRB0	FFh
014Bh			FFh
014Ch	Timer RD General Register C0	TRDGRC0	FFh
014Dh			FFh
014Eh	Timer RD General Register D0	TRDGRD0	FFh
014Fh			FFh
0150h	Timer RD Control Register 1	TRDCR1	00h
0151h	Timer RD I/O Control Register A1	TRDIORA1	10001000b
0152h	Timer RD I/O Control Register C1	TRDIORC1	10001000b
0153h	Timer RD Status Register 1	TRDSR1	11000000b
0154h	Timer RD Interrupt Enable Register 1	TRDIER1	11100000b
0155h	Timer RD PWM Mode Output Level Control Register 1	TRDPOCR1	11111000b
0156h	Timer RD Counter 1	TRD1	00h
0157h			00h
0158h	Timer RD General Register A1	TRDGRA1	FFh
0159h			FFh
015Ah	Timer RD General Register B1	TRDGRB1	FFh
015Bh			FFh
015Ch	Timer RD General Register C1	TRDGRC1	FFh
015Dh			FFh
015Eh	Timer RD General Register D1	TRDGRD1	FFh
015Fh			FFh
0160h	UART1 Transmit/Receive Mode Register	U1MR	00h
0161h	UART1 Bit Rate Register	U1BRG	XXh
0162h	UART1 Transmit Buffer Register	U1TB	XXh
0163h			XXh
0164h	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
0165h	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
0166h	UART1 Receive Buffer Register	U1RB	XXh
0167h			XXh
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h	Timer RG Mode Register	TRGMR	01000000b
0171h	Timer RG Count Control Register	TRGCNTC	00h
0172h	Timer RG Control Register	TRGCR	10000000b
0173h	Timer RG Interrupt Enable Register	TRGIER	11110000b
0174h	Timer RG Status Register	TRGSR	11100000b
0175h	Timer RG I/O Control Register	TRGIOR	00h
0176h	Timer RG Counter	TRG	00h
0177h			00h
0178h	Timer RG General Register A	TRGGRA	FFh
0179h			FFh
017Ah	Timer RG General Register B	TRGGRB	FFh
017Bh			FFh
017Ch	Timer RG General Register C	TRGGRC	FFh
017Dh			FFh
017Eh	Timer RG General Register D	TRGGRD	FFh
017Fh			FFh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.8 SFR Information (8) (1)

Address	Register	Symbol	After Reset
01C0h	Address Match Interrupt Register 0	RMAD0	XXh
01C1h			XXh
01C2h			0000XXXXb
01C3h	Address Match Interrupt Enable Register 0	AIER0	00h
01C4h	Address Match Interrupt Register 1	RMAD1	XXh
01C5h			XXh
01C6h			0000XXXXb
01C7h	Address Match Interrupt Enable Register 1	AIER1	00h
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h	Pull-Up Control Register 0	PUR0	00h
01E1h	Pull-Up Control Register 1	PUR1	00h
01E2h	Pull-Up Control Register 2	PUR2	00h
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	Port P1 Drive Capacity Control Register	P1DRR	00h
01F1h	Port P2 Drive Capacity Control Register	P2DRR	00h
01F2h	Drive Capacity Control Register 0	DRR0	00h
01F3h	Drive Capacity Control Register 1	DRR1	00h
01F4h	Drive Capacity Control Register 2	DRR2	00h
01F5h	Input Threshold Control Register 0	VLT0	00h
01F6h	Input Threshold Control Register 1	VLT1	00h
01F7h	Input Threshold Control Register 2	VLT2	00h
01F8h	Comparator B Control Register 0	INTCMP	00h
01F9h			
01FAh	External Input Enable Register 0	INTEN	00h
01FBh	External Input Enable Register 1	INTEN1	00h
01FCh	INT Input Filter Select Register 0	INTF	00h
01FDh	INT Input Filter Select Register 1	INTF1	00h
01FEh	Key Input Enable Register 0	KIEN	00h
01FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		V _{ref} = AV _{CC}		—	—	10	Bit
—	Absolute accuracy	10-bit mode	V _{ref} = AV _{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±3	LSB
			V _{ref} = AV _{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V _{ref} = AV _{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V _{ref} = AV _{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
		8-bit mode	V _{ref} = AV _{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V _{ref} = AV _{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V _{ref} = AV _{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V _{ref} = AV _{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
φAD	A/D conversion clock		4.0 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	—	20	MHz
			3.2 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	—	16	MHz
			2.7 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	—	10	MHz
			2.2 V ≤ V _{ref} = AV _{CC} ≤ 5.5 V ⁽²⁾		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
t _{CONV}	Conversion time	10-bit mode	V _{ref} = AV _{CC} = 5.0 V, φAD = 20 MHz		2.2	—	—	μs
		8-bit mode	V _{ref} = AV _{CC} = 5.0 V, φAD = 20 MHz		2.2	—	—	μs
t _{SAMP}	Sampling time		φAD = 20 MHz		0.8	—	—	μs
I _{Vref}	V _{ref} current		V _{CC} = 5.0 V, XIN = f1 = φAD = 20 MHz		—	45	—	μA
V _{ref}	Reference voltage				2.2	—	AV _{CC}	V
V _{IA}	Analog input voltage ⁽³⁾				0	—	V _{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ φAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:

1. $V_{CC}/AV_{CC} = V_{ref} = 2.2$ to 5.5 V , $V_{SS} = 0\text{ V}$, and $T_{opr} = -20$ to $85\text{ }^{\circ}\text{C}$ (N version)/ -40 to $85\text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		1,000 ⁽³⁾	—	—	times
—	Byte program time		—	80	500	μs
—	Block erase time		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly stopped until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁷⁾	Ambient temperature = 55 °C	20	—	—	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly stopped until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		−20 ⁽⁷⁾	—	85	°C
—	Data hold time ⁽⁸⁾	Ambient temperature = 55 °C	20	—	—	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. −40 °C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

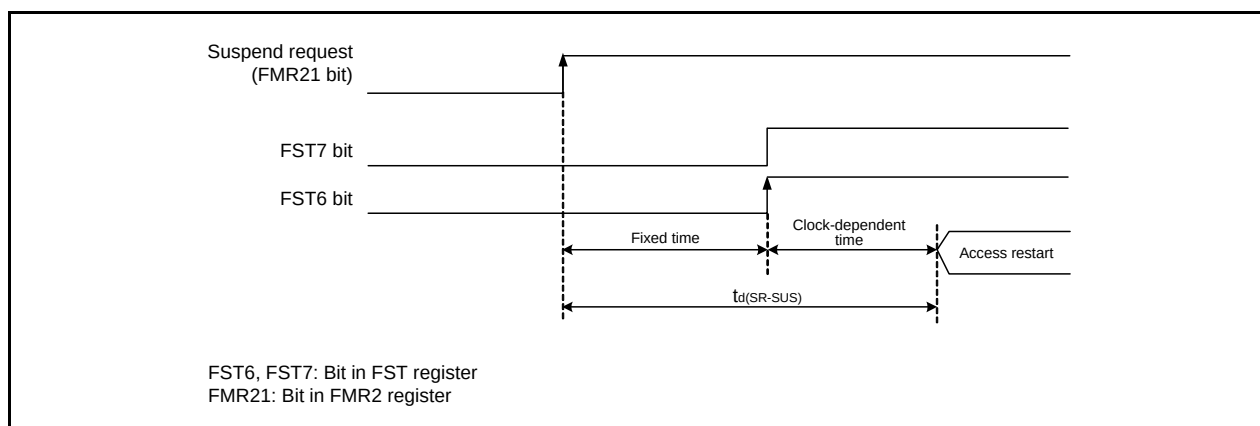
**Figure 5.2 Time delay until Suspend**

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vdet0	Voltage detection level Vdet0_0 ⁽²⁾		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 ⁽²⁾		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 ⁽²⁾		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 ⁽²⁾		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time ⁽⁴⁾	At the falling of Vcc from 5.0 V to (Vdet0_0 – 0.1) V	—	6	150	μs
—	Voltage detection circuit self power consumption	VCA25 = 1, Vcc = 5.0 V	—	1.5	—	μA
td(E-A)	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

Notes:

1. The measurement condition is Vcc = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes Vdet0.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vdet1	Voltage detection level Vdet1_0 ⁽²⁾	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 ⁽²⁾	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 ⁽²⁾	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 ⁽²⁾	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 ⁽²⁾	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 ⁽²⁾	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 ⁽²⁾	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 ⁽²⁾	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 ⁽²⁾	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 ⁽²⁾	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A ⁽²⁾	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B ⁽²⁾	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C ⁽²⁾	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D ⁽²⁾	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E ⁽²⁾	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F ⁽²⁾	At the falling of Vcc	4.20	4.45	4.75	V
—	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time ⁽³⁾	At the falling of Vcc from 5.0 V to (Vdet1_0 – 0.1) V	—	60	150	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, Vcc = 5.0 V	—	1.7	—	μA
td(E-A)	Waiting time until voltage detection circuit operation starts ⁽⁴⁾		—	—	100	μs

Notes:

1. The measurement condition is Vcc = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes Vdet1.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	38.4	40	41.6	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register ⁽²⁾	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	35.389	36.864	38.338	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-20 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	30.72	32	33.28	MHz
		$V_{CC} = 1.8 \text{ V to } 5.5 \text{ V}$ $-40 \text{ }^{\circ}\text{C} \leq T_{opr} \leq 85 \text{ }^{\circ}\text{C}$	30.40	32	33.60	MHz
—	Oscillation stability time	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25 \text{ }^{\circ}\text{C}$	—	0.5	3	ms
—	Self power consumption at oscillation	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25 \text{ }^{\circ}\text{C}$	—	400	—	μA

Notes:

1. $V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to $85 \text{ }^{\circ}\text{C}$ (N version)/ -40 to $85 \text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25 \text{ }^{\circ}\text{C}$	—	30	100	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0 \text{ V}$, $T_{opr} = 25 \text{ }^{\circ}\text{C}$	—	2	—	μA

Note:

1. $V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to $85 \text{ }^{\circ}\text{C}$ (N version)/ -40 to $85 \text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{d(P-R)}	Time for internal power supply stabilization during power-on ⁽²⁾		—	—	2,000	μs

Notes:

1. The measurement condition is $V_{CC} = 1.8$ to 5.5 V and $T_{opr} = 25 \text{ }^{\circ}\text{C}$.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

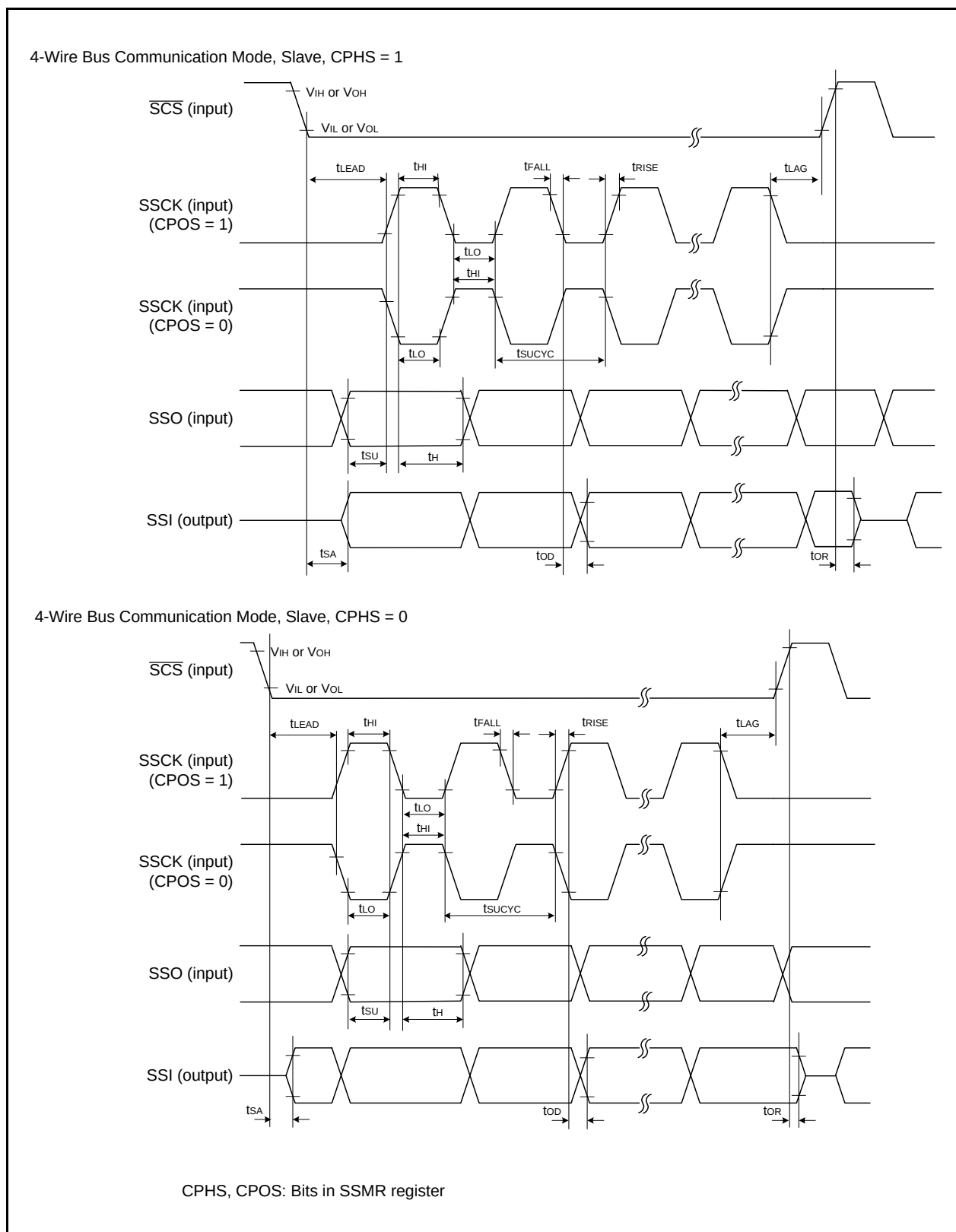


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

Table 5.17 Electrical Characteristics (1) [4.2 V ≤ V_{CC} ≤ 5.5 V]

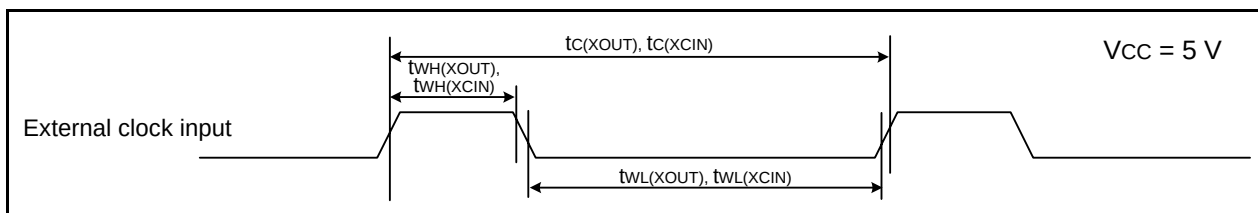
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Other than XOUT	Drive capacity High V _{CC} = 5 V	I _{OH} = -20 mA	V _{CC} - 2.0	—	V _{CC}	V
			Drive capacity Low V _{CC} = 5 V	I _{OH} = -5 mA	V _{CC} - 2.0	—	V _{CC}	V
		XOUT	V _{CC} = 5 V	I _{OH} = -200 μA	1.0	—	V _{CC}	V
V _{OL}	Output "L" voltage	Other than XOUT	Drive capacity High V _{CC} = 5 V	I _{OL} = 20 mA	—	—	2.0	V
			Drive capacity Low V _{CC} = 5 V	I _{OL} = 5 mA	—	—	2.0	V
		XOUT	V _{CC} = 5 V	I _{OL} = 200 μA	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	INT0, INT1, INT2, INT3, INT4, K10, K11, K12, K13, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, TRGIOA, TRGIOB, ADTRG, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	1.2	—	V
		RESET			0.1	1.2	—	V
I _{IH}	Input "H" current		V _I = 5 V, V _{CC} = 5.0 V		—	—	5.0	μA
I _{IL}	Input "L" current		V _I = 0 V, V _{CC} = 5.0 V		—	—	-5.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V, V _{CC} = 5.0 V		25	50	100	kΩ
R _{FXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R _{FXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:

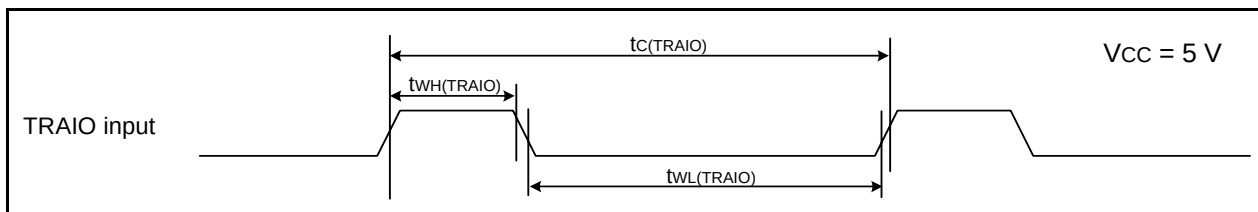
- 4.2 V ≤ V_{CC} ≤ 5.5 V, T_{opr} = -20 to 85 °C (N version)/-40 to 85 °C (D version), and f(XIN) = 20 MHz, unless otherwise specified.

Timing Requirements (Unless Otherwise Specified: $V_{CC} = 5\text{ V}$, $V_{SS} = 0\text{ V}$, $T_{opr} = 25\text{ }^{\circ}\text{C}$)**Table 5.19 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	—	ns
$t_{WH(XOUT)}$	XOUT input "H" width	24	—	ns
$t_{WL(XOUT)}$	XOUT input "L" width	24	—	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	—	μs
$t_{WH(XCIN)}$	XCIN input "H" width	7	—	μs
$t_{WL(XCIN)}$	XCIN input "L" width	7	—	μs

**Figure 5.8 External Clock Input Timing Diagram when $V_{CC} = 5\text{ V}$** **Table 5.20 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	—	ns
$t_{WH(TRAIO)}$	TRAIO input "H" width	40	—	ns
$t_{WL(TRAIO)}$	TRAIO input "L" width	40	—	ns

**Figure 5.9 TRAIO Input Timing Diagram when $V_{CC} = 5\text{ V}$** **Table 5.21 TRFI Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRFI)}$	TRFI input cycle time	400 (1)	—	ns
$t_{WH(TRFI)}$	TRFI input "H" width	200 (2)	—	ns
$t_{WL(TRFI)}$	TRFI input "L" width	200 (2)	—	ns

Notes:

1. When using timer RF input capture mode, adjust the cycle time to $(1/\text{timer RF count source frequency} \times 3)$ or above.
2. When using timer RF input capture mode, adjust the pulse width to $(1/\text{timer RF count source frequency} \times 1.5)$ or above.

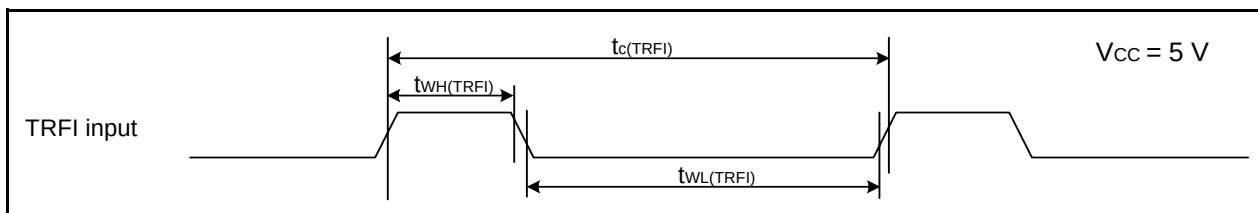
**Figure 5.10 TRFI Input Timing Diagram when $V_{CC} = 5\text{ V}$**

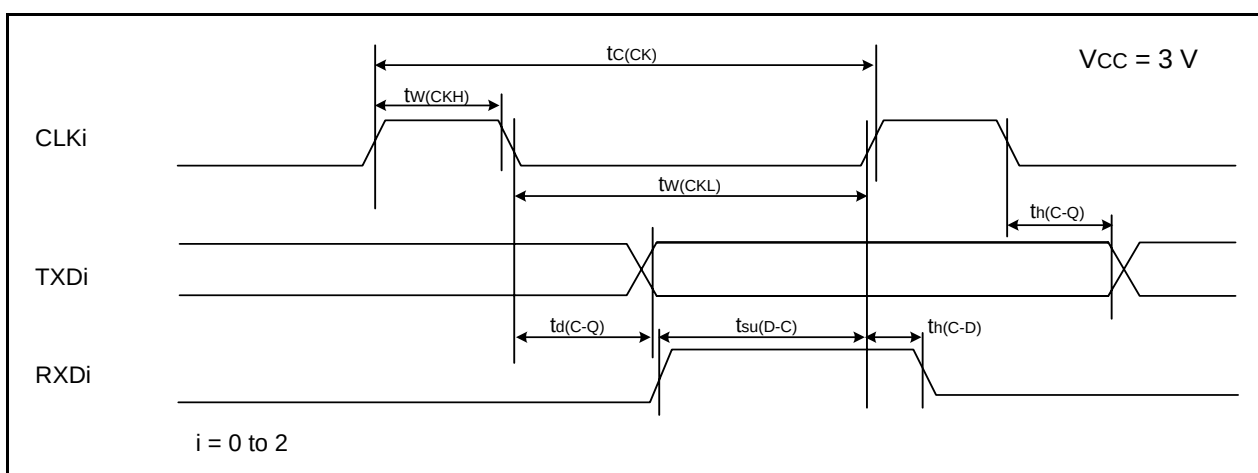
Table 5.25 Electrical Characteristics (4) [$2.7\text{ V} \leq V_{CC} \leq 3.3\text{ V}$]
($T_{opr} = -20\text{ to }85\text{ }^{\circ}\text{C}$ (N version)/ $-40\text{ to }85\text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I _{CC}	Power supply current ($V_{CC} = 2.7\text{ to }3.3\text{ V}$) Single-chip mode, output pins are open, other pins are V _{SS}	High-speed clock mode	—	3.5	10	mA
		High-speed on-chip oscillator mode	—	1.5	7.5	mA
		High-speed on-chip oscillator mode	—	7.0	15	mA
		Low-speed on-chip oscillator mode	—	90	390	μA
		Low-speed clock mode	—	80	400	μA
		Wait mode	—	15	90	μA
		Stop mode	—	2.0	5.0	μA

Table 5.29 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	—	ns
$t_{w(CKH)}$	CLKi input "H" width	150	—	ns
$t_{w(CKL)}$	CLKi Input "L" width	150	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	70	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

**Figure 5.16 Serial Interface Timing Diagram when Vcc = 3 V****Table 5.30 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{Kli}$ (i = 0 to 3)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width, $\overline{Kli}$ input "H" width	380 (1)	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width, $\overline{Kli}$ input "L" width	380 (2)	—	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency $\times$ 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency $\times$ 3) or the minimum value of standard, whichever is greater.

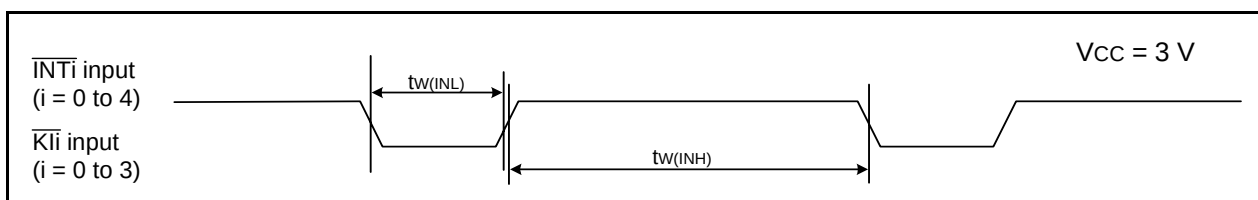
**Figure 5.17 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{Kli}$ when Vcc = 3 V**

Table 5.31 Electrical Characteristics (5) [$1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Other than XOUT	Drive capacity High	I _{OH} = -2 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity Low	I _{OH} = -1 mA	V _{CC} - 0.5	—	V _{CC}	V
		XOUT		I _{OH} = -200 μ A	1.0	—	V _{CC}	V
V _{OL}	Output "L" voltage	Other than XOUT	Drive capacity High	I _{OL} = 2 mA	—	—	0.5	V
			Drive capacity Low	I _{OL} = 1 mA	—	—	0.5	V
		XOUT		I _{OL} = 200 μ A	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	$\overline{\text{NT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT2}}$, $\overline{\text{INT3}}$, $\overline{\text{INT4}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, $\overline{\text{TRAIO}}$, $\overline{\text{TRBO}}$, $\overline{\text{TRCIOA}}$, $\overline{\text{TRCIOB}}$, $\overline{\text{TRCI0C}}$, $\overline{\text{TRCI0D}}$, $\overline{\text{TRDIOA0}}$, $\overline{\text{TRDIOB0}}$, $\overline{\text{TRDIO0C}}$, $\overline{\text{TRDIO0D}}$, $\overline{\text{TRDIOA1}}$, $\overline{\text{TRDIOB1}}$, $\overline{\text{TRDIO0C1}}$, $\overline{\text{TRDIO0D1}}$, $\overline{\text{TRCTRG}}$, $\overline{\text{TRCCLK}}$, $\overline{\text{TRFI}}$, $\overline{\text{TRGIOA}}$, $\overline{\text{TRGIOB}}$, $\overline{\text{ADTRG}}$, $\overline{\text{RXD0}}$, $\overline{\text{RXD1}}$, $\overline{\text{RXD2}}$, $\overline{\text{CLK0}}$, $\overline{\text{CLK1}}$, $\overline{\text{CLK2}}$, $\overline{\text{SSI}}$, $\overline{\text{SCL}}$, $\overline{\text{SDA}}$, $\overline{\text{SSO}}$			0.05	0.20	—	V
		$\overline{\text{RESET}}$			0.05	0.20	—	V
I _{IH}	Input "H" current		V _I = 2.2 V, V _{CC} = 2.2 V		—	—	4.0	μ A
I _{IL}	Input "L" current		V _I = 0 V, V _{CC} = 2.2 V		—	—	-4.0	μ A
R _{PULLUP}	Pull-up resistance		V _I = 0 V, V _{CC} = 2.2 V		70	140	300	k Ω
R _{FXIN}	Feedback resistance	XIN			—	0.3	—	M Ω
R _{FXCIN}	Feedback resistance	XCIN			—	8	—	M Ω
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:

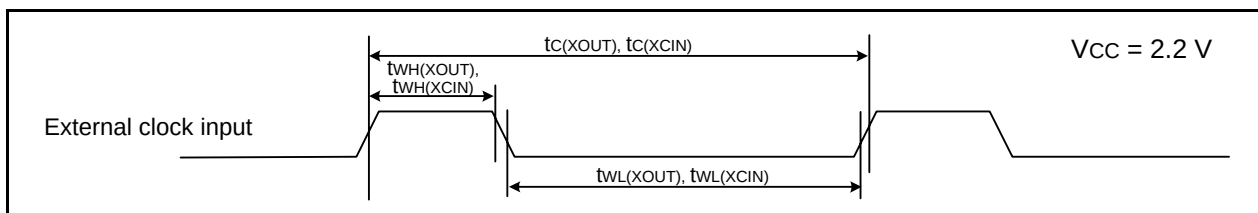
1. $1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$, T_{opr} = -20 to 85 °C (N version)/-40 to 85 °C (D version), and f(XIN) = 5 MHz, unless otherwise specified.

Table 5.32 Electrical Characteristics (6) [$1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$]**($T_{opr} = -20\text{ to }85\text{ }^{\circ}\text{C}$ (N version)/ $-40\text{ to }85\text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.)**

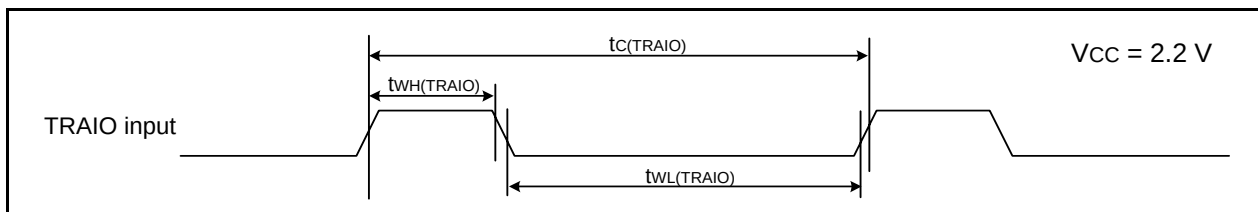
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I _{CC}	Power supply current ($V_{CC} = 1.8\text{ to }2.7\text{ V}$) Single-chip mode, output pins are open, other pins are V _{SS}	High-speed clock mode	—	2.2	—	mA
		XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division				
		XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8				
		High-speed on-chip oscillator mode	—	2.5	10	mA
		XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division				
		XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8				
		XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1				
		Low-speed on-chip oscillator mode	—	90	300	μA
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0				
		Low-speed clock mode	—	80	350	μA
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0				
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0				
		Wait mode	—	15	90	μA
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1				
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1				
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1				
		Stop mode	—	2.0	5	μA
		XIN clock off, $T_{opr} = 25\text{ }^{\circ}\text{C}$ High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0				
		XIN clock off, $T_{opr} = 85\text{ }^{\circ}\text{C}$ High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0				

Timing requirements (Unless Otherwise Specified: $V_{CC} = 2.2\text{ V}$, $V_{SS} = 0\text{ V}$, $T_{opr} = 25\text{ }^{\circ}\text{C}$)**Table 5.33 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_c(XOUT)$	XOUT input cycle time	200	—	ns
$t_{WH}(XOUT)$	XOUT input "H" width	90	—	ns
$t_{WL}(XOUT)$	XOUT input "L" width	90	—	ns
$t_c(XCIN)$	XCIN input cycle time	14	—	μs
$t_{WH}(XCIN)$	XCIN input "H" width	7	—	μs
$t_{WL}(XCIN)$	XCIN input "L" width	7	—	μs

**Figure 5.18 External Clock Input Timing Diagram when $V_{CC} = 2.2\text{ V}$** **Table 5.34 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_c(TRAIO)$	TRAIO input cycle time	500	—	ns
$t_{WH}(TRAIO)$	TRAIO input "H" width	200	—	ns
$t_{WL}(TRAIO)$	TRAIO input "L" width	200	—	ns

**Figure 5.19 TRAIO Input Timing Diagram when $V_{CC} = 2.2\text{ V}$** **Table 5.35 TRFI Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_c(TRFI)$	TRFI input cycle time	2000 (1)	—	ns
$t_{WH}(TRFI)$	TRFI input "H" width	1000 (2)	—	ns
$t_{WL}(TRFI)$	TRFI input "L" width	1000 (2)	—	ns

Notes:

1. When using timer RF input capture mode, adjust the cycle time to $(1/\text{timer RF count source frequency} \times 3)$ or above.
2. When using timer RF input capture mode, adjust the pulse width to $(1/\text{timer RF count source frequency} \times 1.5)$ or above.

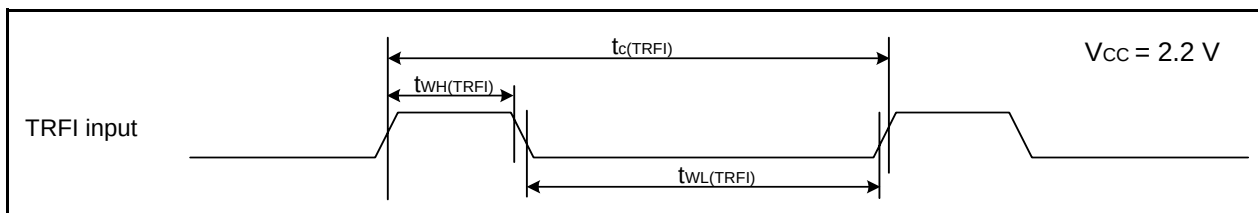
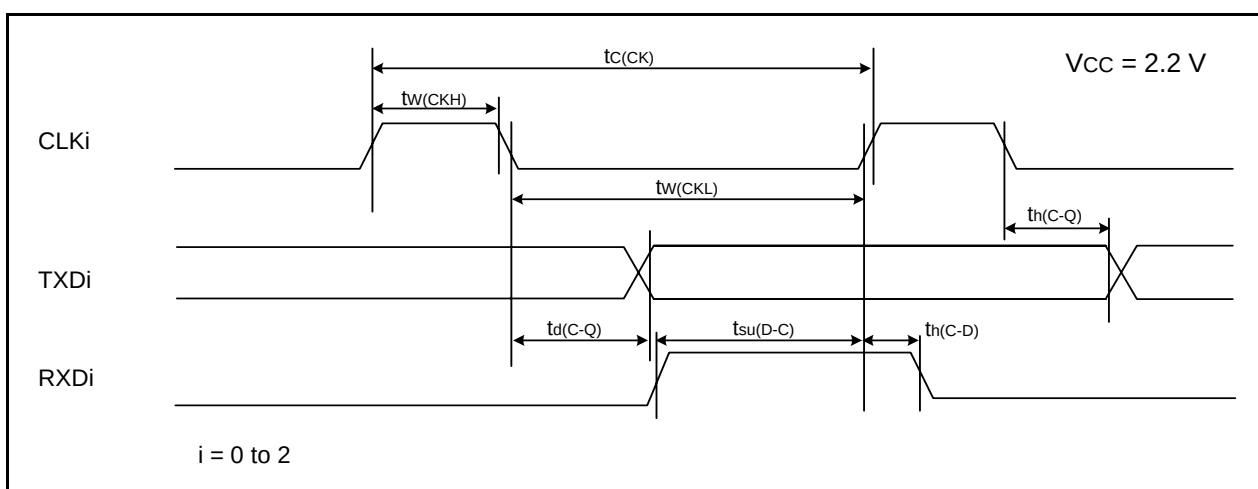
**Figure 5.20 TRFI Input Timing Diagram when $V_{CC} = 2.2\text{ V}$**

Table 5.36 Serial Interface

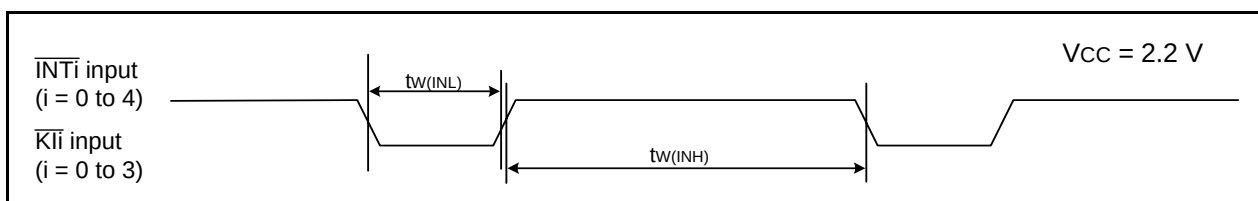
Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{w(CKH)}$	CLKi input "H" width	400	—	ns
$t_{w(CKL)}$	CLKi input "L" width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

 $i = 0 \text{ to } 2$ **Figure 5.21 Serial Interface Timing Diagram when $V_{CC} = 2.2 \text{ V}$** **Table 5.37 External Interrupt $\overline{INTi}$ ($i = 0 \text{ to } 4$) Input, Key Input Interrupt $\overline{Kli}$ ($i = 0 \text{ to } 3$)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width, $\overline{Kli}$ input "H" width	1000 (1)	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width, $\overline{Kli}$ input "L" width	1000 (2)	—	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.

**Figure 5.22 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{Kli}$ when $V_{CC} = 2.2 \text{ V}$**

REVISION HISTORY	R8C/38C Group Datasheet
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Rev.	Date	Description	
		Page	Summary
0.01	Oct 30, 2009	—	First Edition issued
1.00	Apr 23, 2010	All pages 4 27 to 53	“Preliminary”, “Under development” deleted Table 1.3 revised “5. Electrical Characteristics” added
1.10	Nov 02, 2010	— 3 4 5 15 31 45 49 53	TN-R8C-A015A/E reflected Table 1.2 “Timer RG” revised Table 1.3 revised Figure 1.1 revised Figure 3.1 revised Table 5.3 “tCONV”, “tSAMP” revised Table 5.21 revised Table 5.28 revised Table 5.35 revised

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